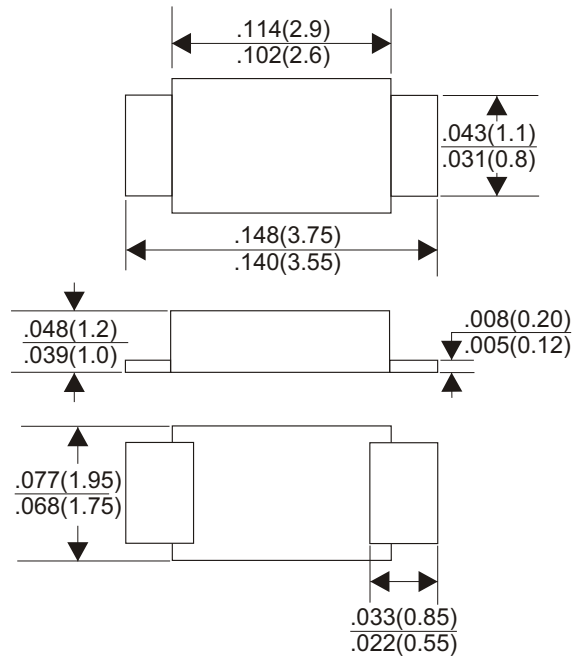




FEATURES

- For surface mounted applications
- Glass Passivated Chip Junction
- Fast reverse recovery time
- Ideal for automated placement
- Lead free in comply with EU RoHS 2011/65/EU directives

SOD123FL



Dimensions in inches and (millimeters)

Absolute Maximum Ratings at 25 °C

Parameter	Symbols	BAV21WL	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	250	V
Maximum RMS voltage	V_{RMS}	200	V
Continuous Forward Current	I_F	250	mA
Repetitive Peak Forward Current	I_{FRM}	625	mA
Non-reptitive Peak Forward Surge Current at 1s at 1ms at 1 us	I_{FSM}	1 3 9	A
Total Power Dissipation	P_{tot}	500	mW
Operating and Storage Temperature Range	T_j, T_{stg}	-55 ~ +150	°C

BAV21WL

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbols	BAV21WL	Units
Reverse Breakdown Voltage at $I_R=100\mu\text{A}$	$V_{(BR)R}$	250	V
Maximum Forward Voltage at 100 m A at 200 m A	V_F	1.00 1.25	V
Maximum DC Reverse Current at Rated DC Blocking Voltage $T_a = 25\text{ }^{\circ}\text{C}$ $T_a = 150\text{ }^{\circ}\text{C}$	I_R	0.1 100	μA
Typical Junction Capacitance at $V_R=4\text{V}$, $f=1\text{MHz}$	C_j	5	pF
Maximum Reverse Recovery Time	t_{rr}	50	ns

RATING AND CHARACTERISTIC CURVES (BAV21WL)

Fig.1 Forward Current Derating Curve

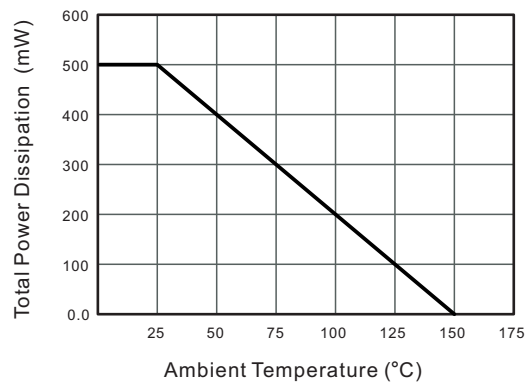


Fig.2 Typical Reverse Characteristics

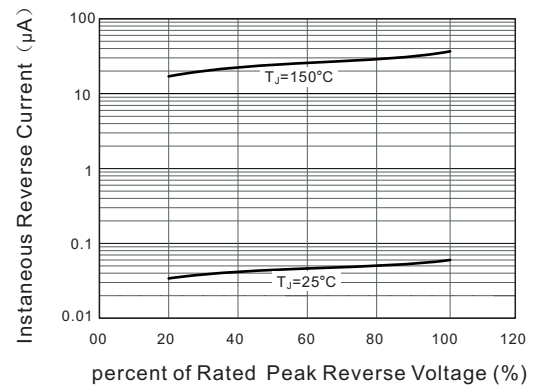


Fig.3 Typical Instantaneous Forward Characteristics

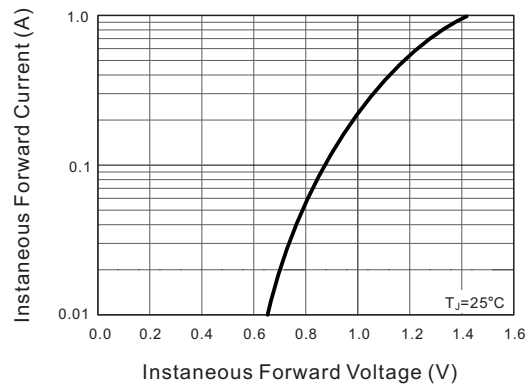


Fig.4 Typical Junction Capacitance

